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Substitute for form 1449A/PTO Application Number 10/709,780 Filing Date 05/27/2004 First Named Inventor Davis Andrew McClure et al. Art Unit 2811 Examiner Name

(Use as many sheets as necessary)

Sheet 1 of 2 Attorney Docket Number 5000.238A

	•		U.S. PATENT	DOCUMENTS	•
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (F troone)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Substitute fo	or form 1449B/PTO			Complete If Known		
				Application Number	10/709,780	
INFO	RMATION D	ISCLO	SURE	Filing Date	05/27/2004	
STAT	TEMENT BY	APPLI	CANT	First Named Inventor	Davis Andrew McClure et al.	
				Art Unit	2811	
	(Use as many sheets	es necessary)		Examiner Name		
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